

8. (Amended) A method of forming a film, comprising the steps of:
- (a) forming a film from a center region of a wafer by supplying a reaction gas at a first flow rate, while a thickness of the film is equal to or thinner than 10 nm; and
- Q2 (b) forming the film on said wafer, by starting to supply the reaction gas at a second flow rate, after said step (a), while continuing to supply the reaction gas at said first flow rate.
9. (Amended) The method according to claim 8, wherein
- said first flow rate is in a range of one fifth to one tenth of said second flow rate.
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